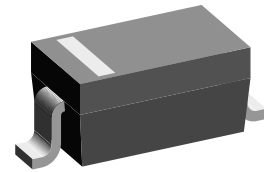


Small Signal Diodes

Features

- Silicon Epitaxial Planar Diodes
- For general purpose
- These diodes are also available in other case styles including: the DO-35 case with the type designations BAV19 to BAV21, the MiniMELF case with the type designations BAV100 to BAV103, the SOT-23 case with the type designations BAS19 to BAS21, and the SOD-323 case with type designations BAV19WS to BAV21WS.



Mechanical Data

Case: SOD-123 plastic case

Weight: approx. 10 mg

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box

GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

Parts Table

Part	Type differentiation	Ordering code	Marking	Remarks
BAV19W	$V_R = 100\text{ V}$	BAV19W-GS18 or BAV19W-GS08	A8	Tape and Reel
BAV20W	$V_R = 150\text{ V}$	BAV20W-GS18 or BAV20W-GS08	A9	Tape and Reel
BAV21W	$V_R = 200\text{ V}$	BAV21W-GS18 or BAV21W-GS08	AA	Tape and Reel

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Continuous reverse voltage		BAV19W	V_R	100	V
		BAV20W	V_R	150	V
		BAV21W	V_R	200	V
Repetitive peak voltage		BAV19W	V_{RRM}	120	V
		BAV20W	V_{RRM}	200	V
		BAV21W	V_{RRM}	250	V
DC Forward current	$T_{amb} = 25\text{ }^{\circ}\text{C}$		I_F	250 ¹⁾	mA
Rectified current (average) half wave rectification with resist. load	$T_{amb} = 25\text{ }^{\circ}\text{C}$		$I_{F(AV)}$	200 ¹⁾	A
Repetitive peak forward current	$f \geq 50\text{ Hz}$, $\theta = 180\text{ }^{\circ}\text{C}$, $T_{amb} = 25\text{ }^{\circ}\text{C}$		I_{FRM}	625 ¹⁾	mA
Surge forward current	$t < 1\text{ s}$, $T_j = 25\text{ }^{\circ}\text{C}$		I_{FSM}	1	A
Power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$		P_{tot}	410 ¹⁾	mW

1) Valid provided that leads are kept at ambient temperature

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		$R_{\theta JA}$	375 ¹⁾	$^{\circ}\text{C/W}$
Junction temperature		T_j	150 ¹⁾	$^{\circ}\text{C}$
Storage temperature range		T_S	- 65 to + 150 ¹⁾	$^{\circ}\text{C}$

1) Valid provided that leads are kept at ambient temperature

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 100\text{ mA}$		V_F			1.00	V
	$I_F = 200\text{ mA}$		V_F			1.25	V
Leakage current	$V_R = 100\text{ V}$	BAV19W	I_R			100	nA
	$V_R = 100\text{ V}$, $T_j = 100\text{ }^{\circ}\text{C}$	BAV19W	I_R			15	μA
	$V_R = 150\text{ V}$	BAV20W	I_R			100	nA
	$V_R = 150\text{ V}$, $T_j = 100\text{ }^{\circ}\text{C}$	BAV20W	I_R			15	μA
	$V_R = 200\text{ V}$	BAV21W	I_R			100	nA
	$V_R = 200\text{ V}$, $T_j = 100\text{ }^{\circ}\text{C}$	BAV21W	I_R			15	μA
Dynamic forward resistance	$I_F = 10\text{ mA}$		r_f		5		Ω
Diode capacitance	$V_R = 0$, $f = 1\text{ MHz}$		C_{tot}		1.5		pF
Reverse recovery time	$I_F = 30\text{ mA}$, $I_R = 30\text{ mA}$, $I_{rr} = 3\text{ mA}$, $R_L = 100\text{ }\Omega$		t_{rr}			50	ns

Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

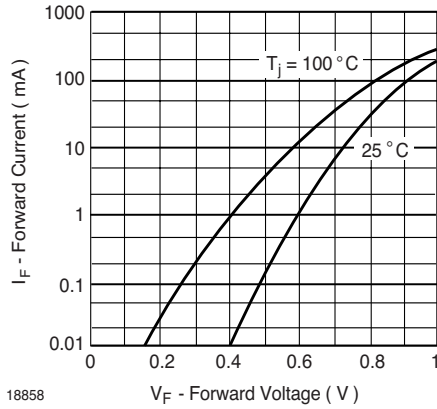


Fig. 1 Forward Current vs. Forward Voltage

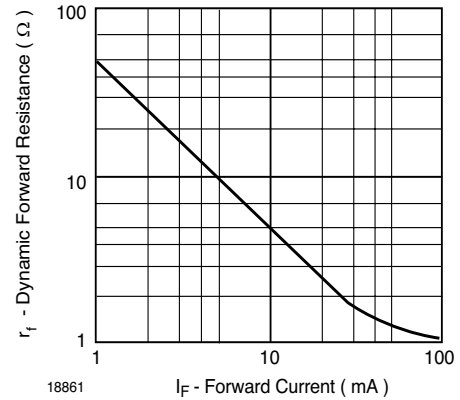


Fig. 4 Dynamic Forward Resistance vs. Forward Current

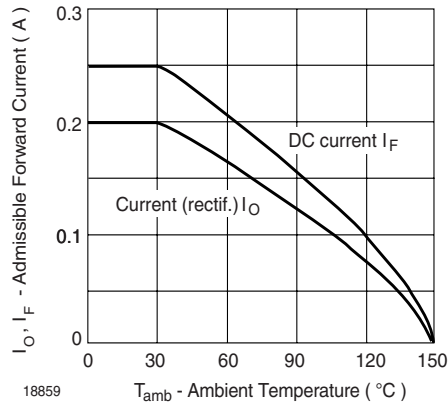


Fig. 2 Admissible Forward Current vs. Ambient Temperature

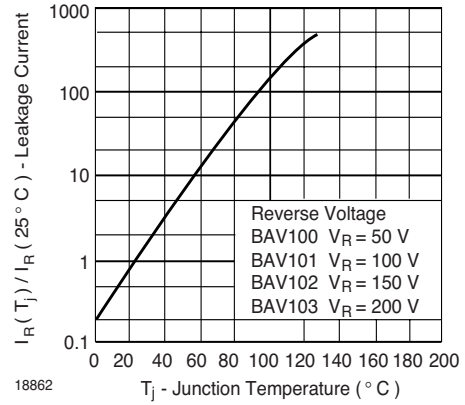


Fig. 5 Leakage Current vs. Junction Temperature

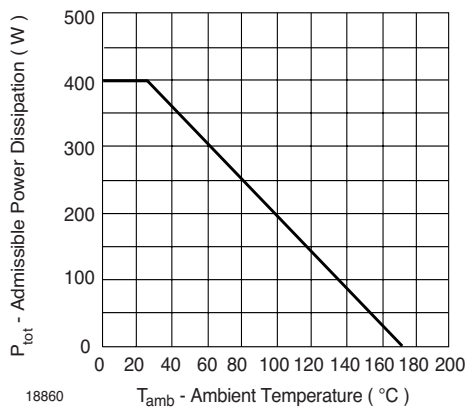


Fig. 3 Admissible Power Dissipation vs. Ambient Temperature

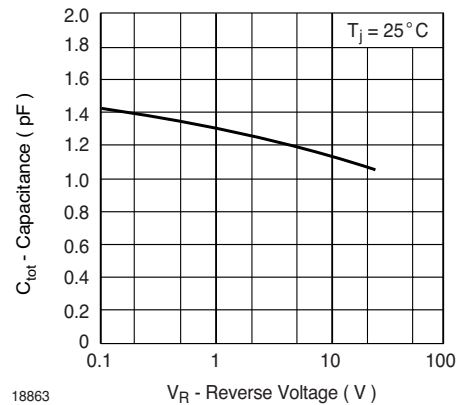


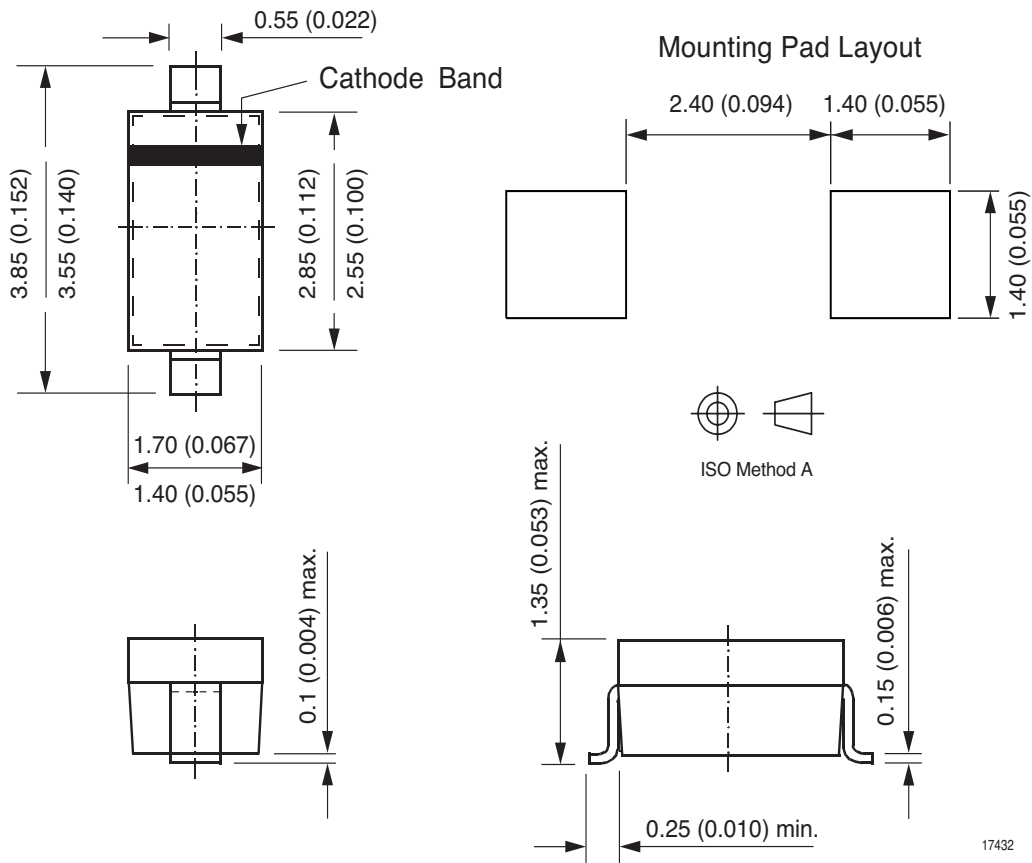
Fig. 6 Capacitance vs. Reverse Voltage

BAV19W / 20W / 21W



Vishay Semiconductors

Package Dimensions in mm (Inches)



17432

**Ozone Depleting Substances Policy Statement**

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423